



11DQ05
11DQ06

SCHOTTKY RECTIFIER

1.1 Amp

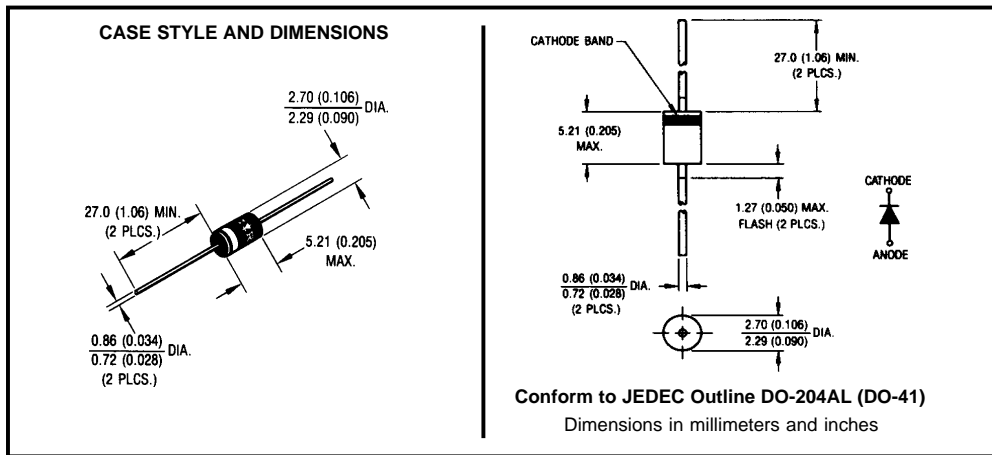
Major Ratings and Characteristics

Characteristics	11DQ..	Units
$I_{F(AV)}$ Rectangular waveform	1.1	A
V_{RRM}	50/60	V
I_{FSM} @ $t_p = 5 \mu s$ sine	150	A
V_F @ 1 Apk, $T_J = 125^\circ C$	0.53	V
T_J range	-40 to 150	$^\circ C$

Description/ Features

The 11DQ.. axial leaded Schottky rectifier has been optimized for very low forward voltage drop, with moderate leakage. Typical applications are in switching power supplies, converters, free-wheeling diodes, and reverse battery protection.

- Low profile, axial leaded outline
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Very low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability



Voltage Ratings

Part number	11DQ05	11DQ06
V_R Max. DC Reverse Voltage (V)	50	60
V_{RWM} Max. Working Peak Reverse Voltage (V)		

Absolute Maximum Ratings

Parameters	11DQ..	Units	Conditions
$I_{F(AV)}$ Max. Average Forward Current * See Fig. 4	1.1	A	50% duty cycle @ $T_C = 84^\circ\text{C}$, rectangular wave form
I_{FSM} Max. Peak One Cycle Non-Repetitive Surge Current * See Fig. 6	150	A	5 μs Sine or 3 μs Rect. pulse
	25		10ms Sine or 6ms Rect. pulse
E_{AS} Non-Repetitive Avalanche Energy	2.0	mJ	$T_J = 25^\circ\text{C}$, $I_{AS} = 1$ Amps, $L = 4$ mH
I_{AR} Repetitive Avalanche Current	1.0	A	Current decaying linearly to zero in 1 μsec Frequency limited by T_J max. $V_A = 1.5 \times V_R$ typical

Electrical Specifications

Parameters	11DQ..	Units	Conditions
V_{FM} Max. Forward Voltage Drop * See Fig. 1 (1)	0.58	V	@ 1A
	0.76	V	@ 2A
	0.53	V	@ 1A
	0.64	V	@ 2A
I_{RM} Max. Reverse Leakage Current * See Fig. 2 (1)	1.0	mA	$T_J = 25^\circ\text{C}$
	11	mA	$T_J = 125^\circ\text{C}$
C_T Typical Junction Capacitance	55	pF	$V_R = 5V_{DC}$ (test signal range 100Khz to 1Mhz) 25°C
L_S Typical Series Inductance	8.0	nH	Measured lead to lead 5mm from package body
dv/dt Max. Voltage Rate of Change	10000	V/ μs	(Rated V_R)

(1) Pulse Width < 300 μs , Duty Cycle <2%

Thermal-Mechanical Specifications

Parameters	11DQ..	Units	Conditions
T_J Max. Junction Temperature Range (*)	-40 to 150	$^\circ\text{C}$	
T_{stg} Max. Storage Temperature Range	-40 to 150	$^\circ\text{C}$	
R_{thJA} Max. Thermal Resistance Junction to Ambient	100	$^\circ\text{C/W}$	DC operation Without cooling fin
R_{thJL} Typical Thermal Resistance Junction to Lead	81	$^\circ\text{C/W}$	DC operation (See Fig. 4)
wt Approximate Weight	0.33(0.012)	g (oz.)	
Case Style	DO-204AL(DO-41)		

(*) $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$ thermal runaway condition for a diode on its own heatsink

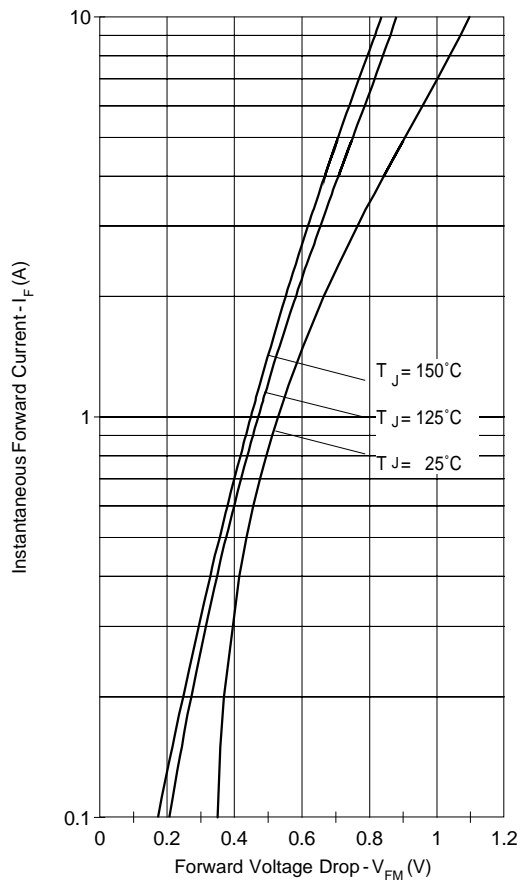


Fig. 1 - Maximum Forward Voltage Drop Characteristics

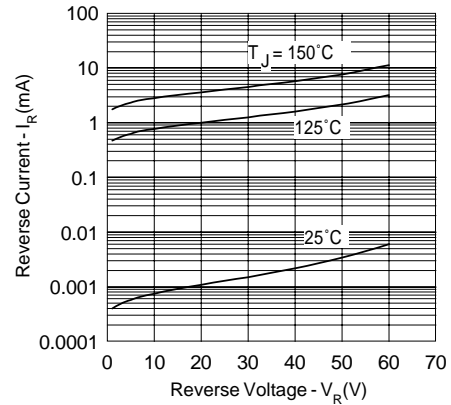


Fig. 2 - Typical Values of Reverse Current Vs. Reverse Voltage

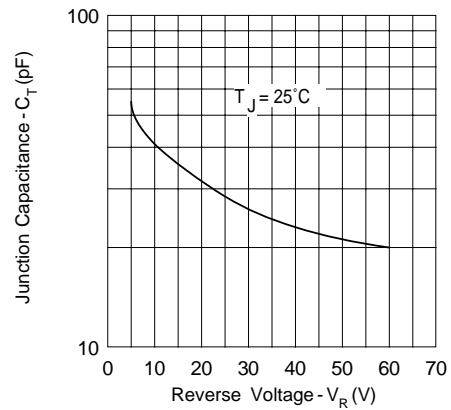


Fig. 3 - Typical Junction Capacitance Vs. Reverse Voltage

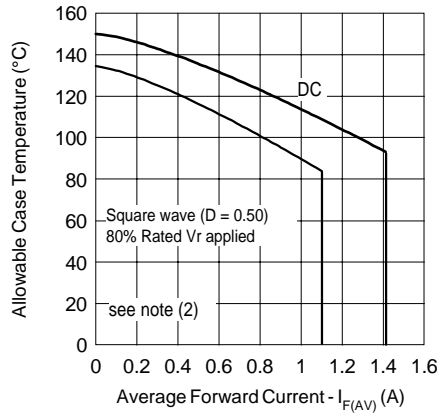


Fig. 4 - Maximum Ambient Temperature Vs. Average Forward Current, Printed Circuit Board Mounted

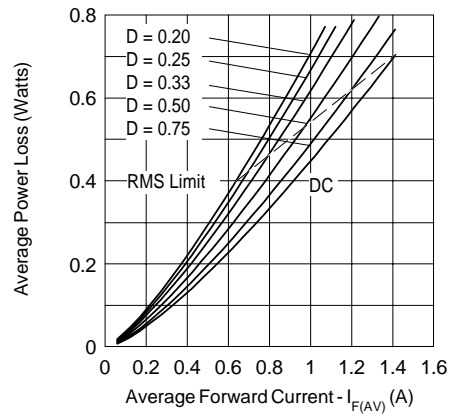


Fig. 5 - Forward Power Loss Characteristics

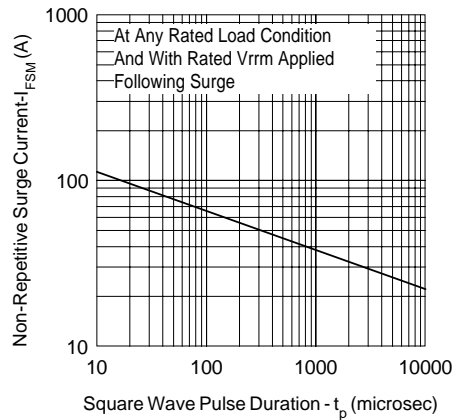
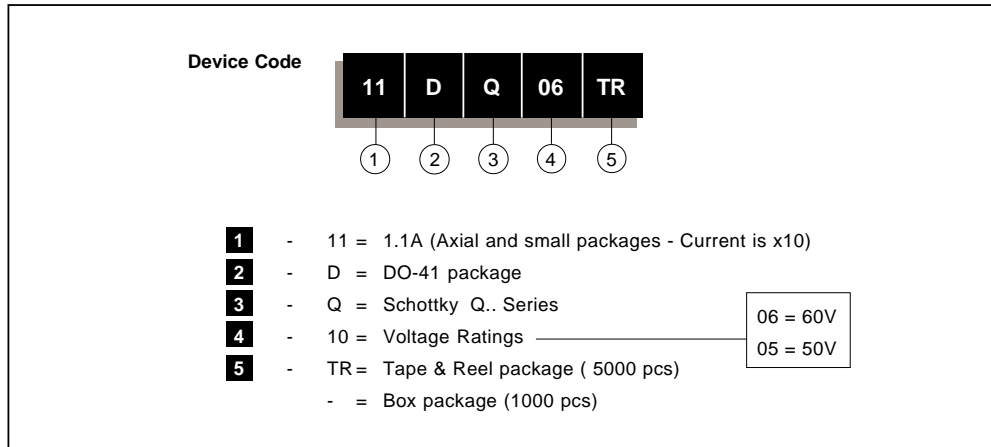


Fig. 6 - Maximum Non-Repetitive Surge Current

- (2) Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;
 $Pd = \text{Forward Power Loss} = I_{F(AV)} \times V_{FM} @ (I_{F(AV)} / D)$ (see Fig. 6);
 $Pd_{REV} = \text{Inverse Power Loss} = V_{R1} \times I_R (1 - D); I_R @ V_{R1} = 80\% \text{ rated } V_R$

Ordering Information Table



Data and specifications subject to change without notice.
 This product has been designed and qualified for Industrial Level.
 Qualification Standards can be found on IR's Web site.